



FZT1151A

40V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -40V
- I_C = -3A High Continuous Collector Current
- I_{CM} = -5A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -140mV @ -1A
- h_{FE} Specified up to -5A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

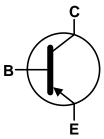
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <a>(3)
- Weight: 0.112 grams (Approximate)

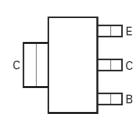




Top View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

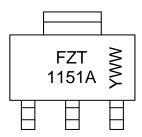
ſ	Part number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	FZT1151ATA	AEC-Q101	FZT1151A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



FZT 1151A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-45	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-40	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	Ісм	-5	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	Б	2.0	W	
Power Dissipation	(Note 7)	P _D	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)		62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1		
	(Note 8)		104		
Thermal Resistance, Junction to Lead (Note 9)		$R_{ hetaJL}$	10.9		
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 10)

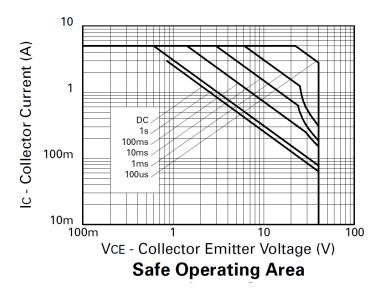
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

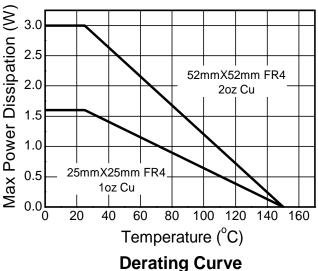
Notes:

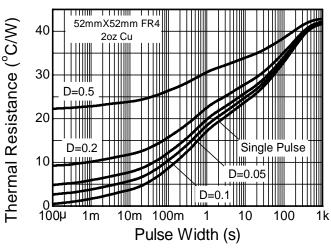
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

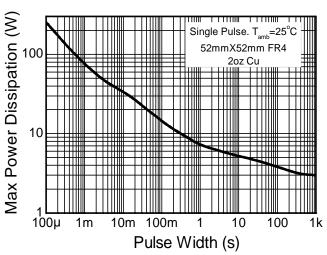


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



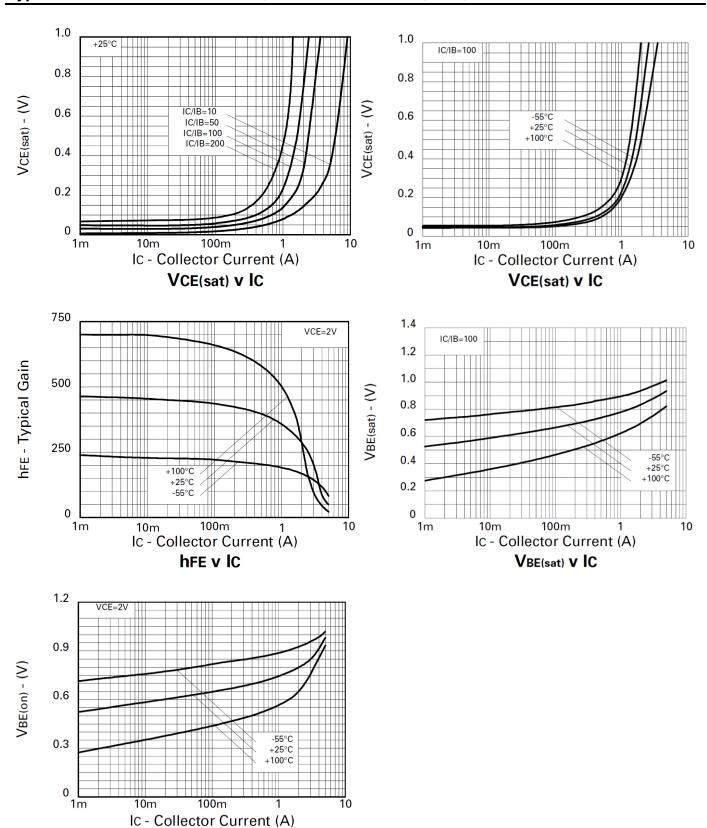
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-45	-95	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CER}	-40	-90	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-40	-85	-	V	I _C = -10mA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEV}	-40	-90	-	V	$I_C = -100\mu A$, $V_{EB} = +1V$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	-	-0.3	-100	nA	V _{CB} = -36V
Emitter Cut-Off Current	I _{EBO}	-	-0.3	-100	nA	$V_{EB} = -4V$
Collector Emitter Cut-Off Current	I _{CEO}	-	-0.3	-100	nA	$V_{CE} = -32V$
		270	450	-	-	$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
	h _{FE}	250	400	800		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Transfer Static Ratio (Note 11)		180	300	-		$I_C = -2A$, $V_{CE} = -2V$
		100	190	-		$I_C = -3A$, $V_{CE} = -2V$
		-	45	-		$I_C = -5A$, $V_{CE} = -2V$
	VCE(sat)	-	-60	-90	mV	$I_C = -100 \text{mA}, I_B = -1.0 \text{mA}$
		-	-120	-180		$I_C = -500 \text{mA}, I_B = -5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)		-	-140	-220		$I_C = -1A$, $I_B = -20mA$
Concetor Entitle Catalation Voltage (Note 11)		-	-170	-260		$I_C = -1.8A$, $I_B = -70mA$
		-	-200	-300		$I_C = -3A$, $I_B = -250mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-985	-1,100	mV	$I_C = -3A$, $I_B = -250mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	-850	-1,000	mV	$I_C = -3A$, $V_{CE} = -2V$
Transitional Frequency (Note 11)	f _T	-	145	-	MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V},$ f = 50 MHz
Output Capacitance	C_obo	-	40	-	pF	$V_{CB} = -10V$, $f = 1MHz$
Switching Time	ton	-	170	-	200	V _{CC} = -30V, I _C = -2A,
Switching Time	t _{OFF}	-	460	-	ns	$I_B = \pm 20 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



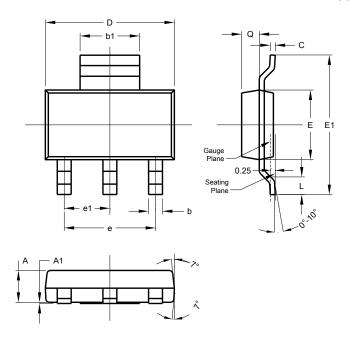
VBE(on) v IC



Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT223

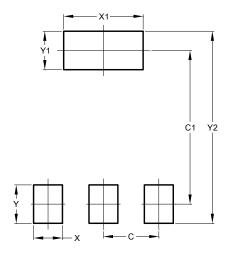


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8 00



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